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		Applicant:	
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jsk	AR	Micron Technology, Inc., "1995 DRAM Data Book" pp. 4-1 thru 4-42, 12/95
ille		 "Rossini, Pentium, PCI-ISA, Chip Set", Symphony Laboratories, entire book.
W	AT	PCT Patent Application No. PCT/US95/16984, filed 12/22/1995, entitled: Burst Edo Memory Device.
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PCT Patent Application No. PCT/US95/16656, filed 12/21/1995, entitled: Burst Edo Memory Device Address Counter.

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